

isc Silicon NPN Power Transistors

2SD676

DESCRIPTION

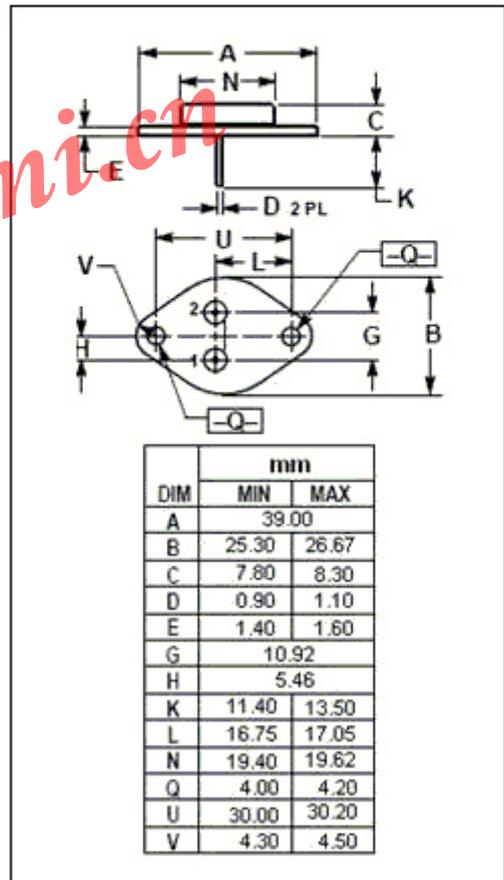
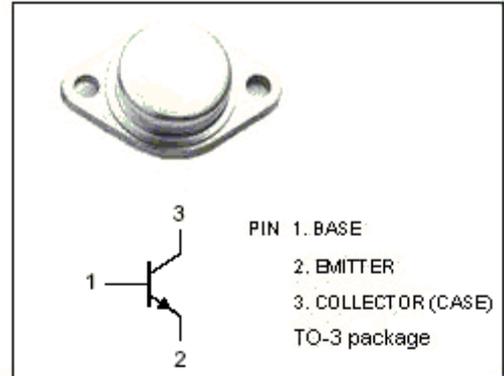
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 160V(\text{Min})$
- High Power Dissipation-
: $P_C = 125W(\text{Max})@T_C = 25^\circ\text{C}$
- Complement to Type 2SB656

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	20	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	125	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistors**2SD676****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA; R _{BE} = ∞	160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 5mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.6A			2.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1A; V _{CE} = 5V			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V; I _E = 0			0.1	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	60		200	
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 5V	20			

◆ **h_{FE-1} Classifications**

B	C
60-120	100-200